

TAI-SAW TECHNOLOGY CO., LTD. No. 3, Industrial 2nd Rd., Ping-Chen Industrial District,

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Product Specifications Approval Sheet

Product Name: GPS L5 Band 1176.45MHz Front-End Module 1.5x1.1 mm(BW=25MHz)

TST Parts No.: TN0126A (This Part is qualified with AEC-Q200)

Customer Part No.:_____

| | Company: | | |
|----|---------------|------------------------|--|
| | Division: | | |
| | Approved by : | | |
| | Date: | | |
| | | | |
| Cł | necked by: | Jerry Xu | |
| Ap | pproval by: | Jerry Xu Ryan Huang | |
| | ate: | 2019/03/29 | |

- 1. Customer signed back is required before TST can proceed with sample build and receive orders.
- 2. Orders received without customer signed back will be regarded as agreement on the specifications.
- 3. Any specifications changes must be approved upon by both parties and a new revision of specifications shall be released to reflect the changes.

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TAI-SAW TECHNOLOGY CO., LTD.

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GPS L5 Band Front-End Module 1.5x1.1 mm

MODEL NO.: TN0126A

A. <u>GENERAL DESCRIPTION</u>:

- 1. The TN0126A is a front-end module (FEM) designed for GPS L5 band applications.
- 2. The TN0126A offers low noise figure, high linearity, and high out-band rejection characteristics brought by included high performance pre-SAW filter and low noise amplifier (LNA).
- 3. The TN0126A offers only two external components, and very small package that is 1.5x1.1mm.

B. <u>RECOMMENDED OPERATING CONDITION</u>: (Ta=25 ℃)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|----------------|-----------------|------|------|------|------|
| Supply Voltage | V _{DD} | 1.5 | - | 3.42 | V |

C. ABSOLUTE MAXIMUM RATINGS:

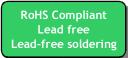
- 1. Supply voltage: V_{DD}=5 V
- 2. Control voltage: V_{CTL}=5 V
- 3. Input power:
 - P_{IN} (inband): +10 dBm(V_{DD}=2.8 V, f=1176.45, 1164~1189 MHz)
 - P_{IN} (outband): +25 dBm(V_{DD}=2.8 V, f=50~1050, 1250~4000 MHz)
- 4. Power dissipation: $P_D=500 \text{ mW}(4\text{-layer FR4 PCB with through-hole}(101.5x114.5 \text{ mm}), Tj=100 ^{\circ}C)$
- 5. Terminating source impedance: Zs = 50 (Single-ended) Terminating load impedance: ZL = 50 (Single-ended)
- 6. Operating temperature range: -40 ℃ to +105 ℃
- 7. Storage temperature range: -40 ℃ to +110 ℃

D. <u>FEATURES</u>:

- 1. Low supply voltage: 1.8/ 2.8 V typ.
- 2. Low current consumption:
 - 3.0/3.7mA typ.(at V_{DD}=1.8/ 2.8 V, V_{CTL}=1.8 V)
 - 0.1µA typ.(at V_{DD}=1.8/ 2.8 V, V_{CTL}=0 V (Stand-by mode))
- 3. High gain: 15.5/16.0dB typ.(at V_{DD}=1.8/2.8 V,V_{CTL}=1.8 V, f=1176.45 MHz, 1164~1189 MHz)
- 4. Low noise figure:
 - 1.65/1.6dB typ.(at V_{DD}=1.8/ 2.8 V, V_{CTL}=1.8 V, f=1176.45 MHz)
- 5. High out band rejection(at V_{DD}=1.8/2.8 V, V_{CTL}=1.8 V):

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TST DCC Release document



REV. NO.:1.0

Electrostatic Sensitive Device (ESD)

2

- 36 dBc typ.(f=704~915 MHz, relative to 1176.45 MHz)
- 40 dBc typ.(f=1710~1980 MHz, relative to 1176.45 MHz)
- 60 dBc typ.(f=2400~2500 MHz, relative to 1176.45 MHz)
- 6. Small package size: HFFP10-CD: 1.5mmx1.1mm (typ.), t=0.5mm (max.)
- 7. Moisture Sensitivity Level: Level 3

E. ELECTRICAL CHARACTERISTICS 1 (DC):

(General conditions: $T_a=+25$ °C)

| Paran | Symbol | Unit | Min. | Тур. | Max. | |
|--|---|---------------------|------|------|------|------|
| Supply Voltage | | V _{DD} | V | 1.5 | - | 3.3 |
| Control Voltage (High | $V_{\text{CTL}(H)}$ | V | 1.5 | 1.8 | 3.3 | |
| Control Voltage (Low) | | V _{CTL(L)} | V | 0 | 0 | 0.3 |
| Supply Current 1 | RF OFF, V _{DD} =2.8 V, V _{CTL} =1.8 V | I _{DD1} | mA | - | 3.7 | - |
| Supply Current 2 | RF OFF, V _{DD} =1.8 V, V _{CTL} =1.8 V | I _{DD2} | mA | - | 3.0 | - |
| Supply Current 3 RF OFF, V _{DD} =2.8 V, V _{CTL} =0 V | | I _{DD3} | μA | - | 0.1 | 3.0 |
| Supply Current 4 | RF OFF, V _{DD} =1.8 V, V _{CTL} =0 V | I _{DD4} | μA | - | 0.1 | 3.0 |
| Control Current | rol Current V _{CTL} =1.8 V | | μA | - | 5.0 | 12.0 |

F. ELECTRICAL CHARACTERISTICS 2 (RF):

(General conditions: V_{DD} =2.8 V, V_{CTL} =1.8 V, f_{RF} =1176.45 MHz, 1164~1189, T_a =+25 °C, Z_s = Z_I =50 ohm, with application circuit)

| Paran | Parameters Description | | | Min. | Тур. | Max. |
|--|---|------------|-----|------|------|------|
| Small Signal Gain (GPS) | f=1176.45MHz (GPS) Exclude PCB, Connector Losses(0.17 dB) | GainGPS1 | dB | - | 18 | - |
| Noise Figure (GPS) | f=1176.45 MHz (GPS) Exclude PCB,Connector Losses (0.09 dB) | NFGPS1 | dB | - | 1.85 | - |
| Input Power at 1dB Gain, Compression Point | f=1176.45 MHz | P-1dB(IN)1 | dBm | - | -9.8 | - |
| Input 3rd Order Intercept Point | f1=1176.45 MHz, f2=f1 +/-1 MHz, Pin=-30 dBm | IIP3_1 | dBm | - | -1.5 | - |
| Low Band Rejection | f=704 to 915 MHz, relative to 1176.45 MHz | BR_L1 | dBc | - | 46 | - |
| GPS, GNS, BeiDou Rejection | f=1559 to 1606 MHz, relative to 1176.45 MHz | BR_G1 | dBc | | 49 | |

| High Band Rejection | f=1710 to 1980 MHz, relative to 1176.45 MHz | BR_H | dBc | - | 59 | - |
|-------------------------------|--|---------|-----|---|-----|---|
| WLAN Band Rejection | f=2400 to 2500 MHz, relative to 1176.45 MHz | BR_W | dBc | - | 69 | - |
| RF IN Return Loss (GPS) | f=1176.45 MHz (GPS L5) | RLiGPS | dB | - | 18 | - |
| RF OUT Return Loss(GPS) | f=1176.45 MHz (GPS L5) | RLoGPS | dB | - | 9.5 | - |
| Group Delay Time Deviation | f=1164 to 1189 MHz (GPS L5) | GDTGLN1 | ns | - | 10 | - |
| | | | | | | |

ELECTRICAL CHARACTERISTICS 3 (RF):

(General conditions: V_{DD} =1.8 V, V_{CTL} =1.8 V, f_{RF} =1176.45 MHz, 1164 to 1189, T_a =+25 °C, Z_s = Z_I =50 ohm, with application circuit)

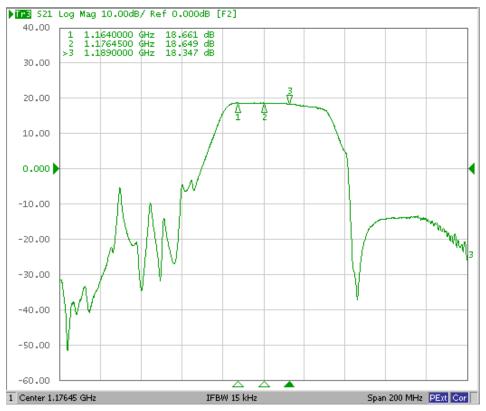
| Para | meters Description | Symbol | Unit | Min. | Тур. | Max. |
|--|---|----------------|------|------|------|------|
| Small Signal Gain (GPS) | f=1176.45MHz (GPS) Exclude PCB, Connector Losses(0.17 dB) | GainGPS 1 | dB | - | 17.5 | - |
| Noise Figure (GPS) | f=1176.45 MHz (GPS) Exclude PCB,Connector Losses (0.09 dB) | NFGPS1 | dB | - | 2.0 | - |
| Input Power at 1dB Gain, Compression Point | f=1176.45 MHz | P-1dB(IN) 1 | dBm | - | -9.8 | - |
| Input 3rd Order Intercept Point | f1=1176.45 MHz, f2=f1 +/-1 MHz, Pin=-30 dBm | IIP3_1 | dBm | - | -1.5 | - |
| Low Band Rejection | f=704 to 915 MHz, relative to 1176.45 MHz | BR_L1 | dBc | - | 46 | - |
| GPS, GNS, BeiDou Rejection | f=1559 to 1606 MHz, relative to 1176.45 MHz | BR_G1 | dBc | | 49 | |
| High Band Rejection | f=1710 to 1980 MHz, relative to 1176.45 MHz | BR_H | dBc | - | 59 | - |
| WLAN Band Rejection | f=2400 to 2500 MHz, relative to 1176.45 MHz | BR_W | dBc | - | 69 | - |
| RF IN Return Loss (GPS) | f=1176.45 MHz (GPS L5) | RLiGPS | dB | - | 15 | - |
| RF OUT Return Loss(GPS) | f=1176.45 MHz (GPS L5) | RLoGPS | dB | - | 8.5 | - |
| Group Delay Time Deviation | f=1164 to 1189 MHz (GPS L5) | GDTGLN | ns | - | 10 | - |
| | | | | | | |

FREQUENCY CHARACTERISTICS 1:

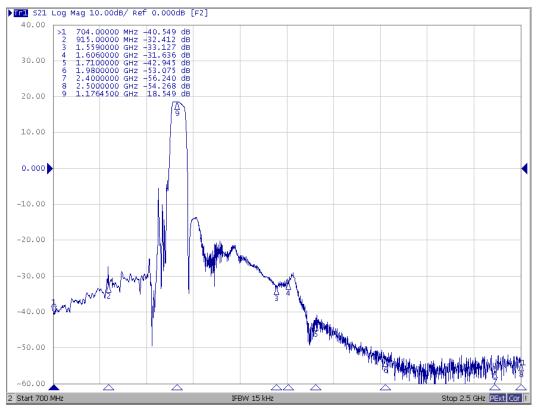
(Conditions: V_{DD} =2.8 V, V_{CTL} =1.8 V, Ta=25 °C, Z_s = Z_I =50 ohm, with application circuit.)

Transfer function:

S21 response (span: 200 MHz)

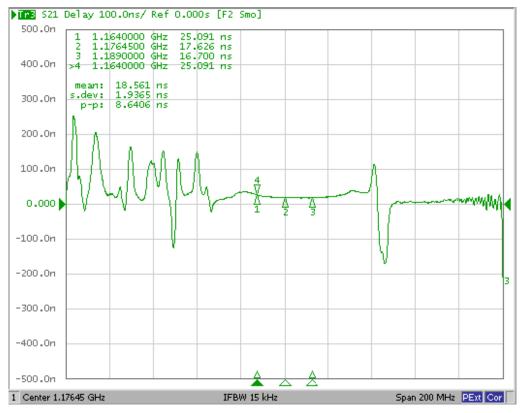


S21 response



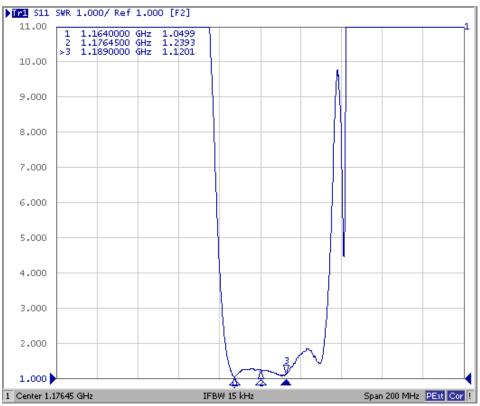
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Group Delay

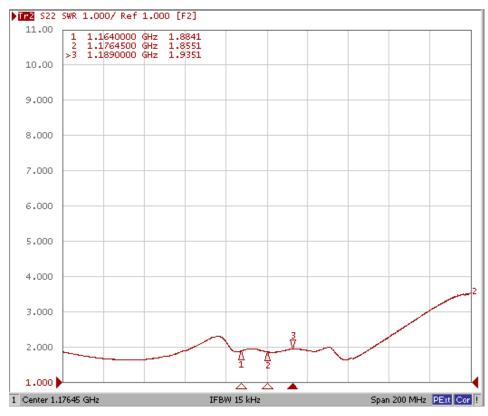


Reflection functions:

S11 VSWR

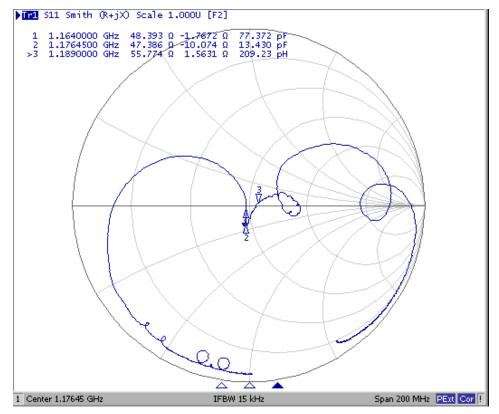


S22 VSWR

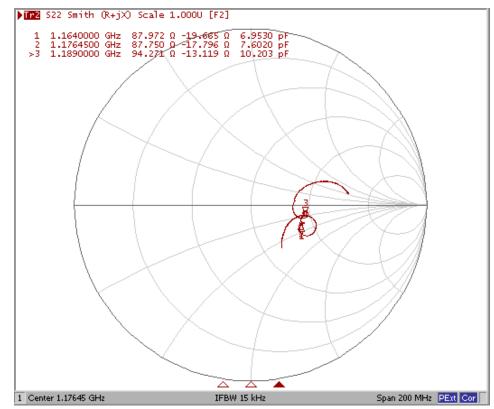


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S11 Smith Chart



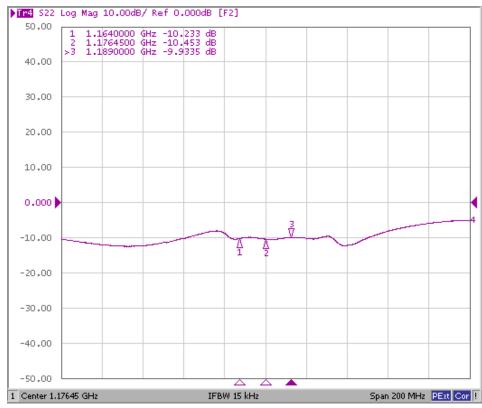
S22 Smith Chart



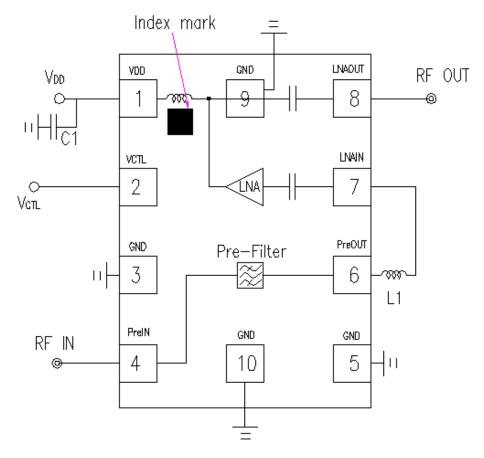
S11 Return Loss



S22 Return Loss



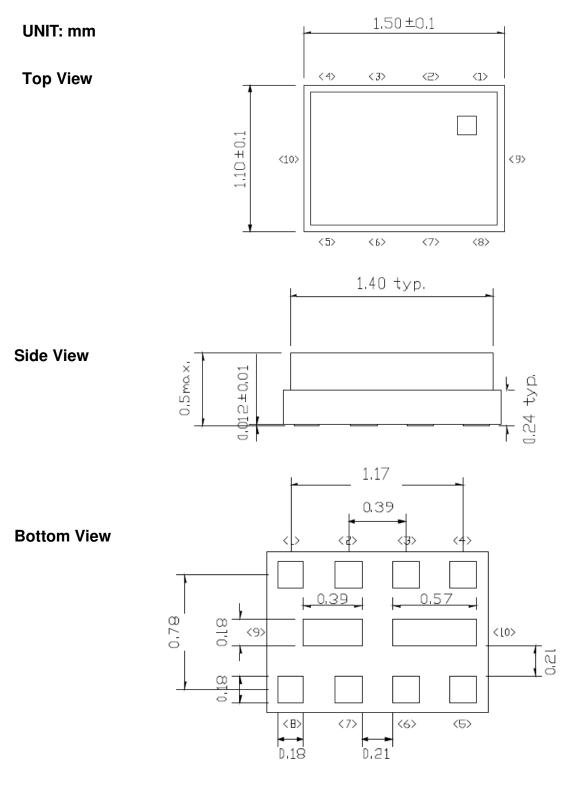
G. MEASUREMENT CIRCUIT:



Top View

| Parts ID | Manufacture | Value |
|----------|--------------------------|--------|
| L1 | Murata LQW15AN_00 Series | 27nH |
| C1 | Murata GRM03 Series | 1000pF |

H. PACKAGE OUTLINE:

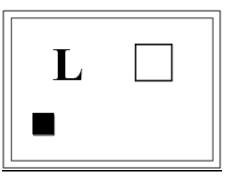


Electrode Dimensions clearance: ±0.05 mm Stand-off: 0.1 mm max. Substrate: Ceramic Terminal treat: Au Lid: SnAg/Kovar/Ni

Weight (typ.): 5 mg

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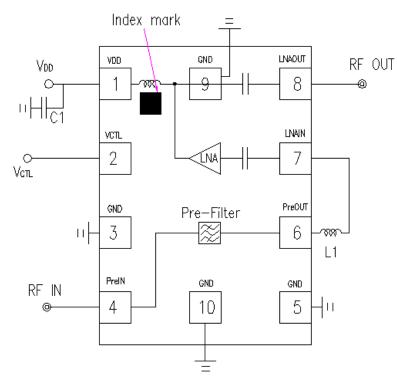
I. OUTLINE DRAWING:



: Year/Month Code (Follow the table)

| YEAR/Month | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 |
|------------|----------|----------|----------|----------|----------|----------|----------|----------|----------|----------|----------|----------|
| 2013 | Α | в | C | D | E | F | U | Н | J | K | L | Μ |
| 2014 | Ν | Р | Ø | R | S | Т | υ | V | W | X | Y | Z |
| 2015 | а | b | C | d | е | f | g | h | j | k | I | m |
| 2016 | n | р | q | r | S | t | u | v | w | X | У | Z |
| 2017 | A | В | C | D | E | F | G | H | <u>J</u> | <u>K</u> | L | M |
| 2018 | N | P | Ø | <u>R</u> | <u>s</u> | <u>T</u> | U | V | W | <u>X</u> | <u>Y</u> | <u>Z</u> |
| 2019 | <u>a</u> | <u>b</u> | <u>c</u> | <u>d</u> | <u>e</u> | <u>f</u> | g | <u>h</u> | j | <u>k</u> | <u> </u> | <u>m</u> |
| 2020 | <u>n</u> | <u>p</u> | <u>q</u> | <u>r</u> | S | <u>t</u> | <u>u</u> | <u>v</u> | W | <u>×</u> | Y | <u>Z</u> |

J. <u>PIN CONFIGURATION</u>:



Top View

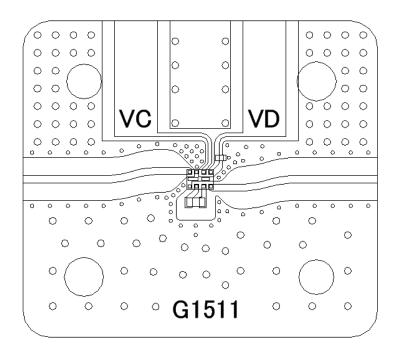
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TRUTH TABLE

| $"H"=V_{CTL}(H), "L"=V_{CTL}(L)$ | | | | | |
|----------------------------------|---------------|--|--|--|--|
| VCTL | Mode | | | | |
| Н | Active mode | | | | |
| L | Stand-by mode | | | | |

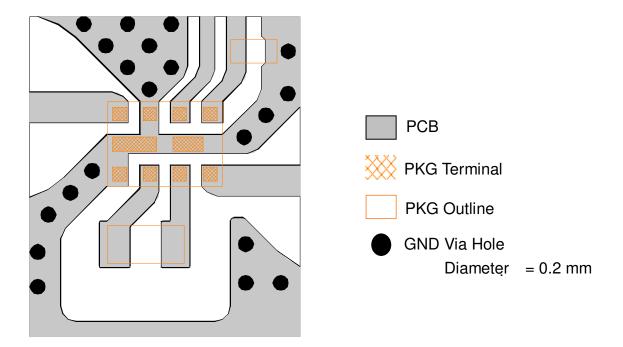
| No. | SYMBOL | DESCRIPTION |
|-----|--------|--|
| 1 | VDD | Supply voltage terminal. Please connect bypass capacitor C1 with ground as close as possible. |
| 2 | VCTL | Control voltage terminal. |
| 3 | GND | Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance. |
| 4 | PreIN | RF input terminal. This terminal connects to input of pre-SAW filter. |
| 5 | GND | Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance. |
| 6 | PreOUT | Pre-SAW filter output terminal. This terminal connects to LNAIN with L1. |
| 7 | LNAIN | RF input terminal. This terminal requires only a matching inductor L1, and does not require DC blocking capacitor because of integrated capacitor. |
| 8 | LNAOUT | RF output terminal. This terminal requires no DC blocking capacitor since this terminal has integrated DC blocking capacitor. |
| 9 | GND | Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance. |
| 10 | GND | Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance. |

K. EVALUATION BOARD:



PCB Substrate: TLX-9 Thickness: 0.12 mm Microstrip line width: 0.322 mm(Z_0 =50 Ω) Size: 14.0 mm x 14.0 mm

<PCB LAYOUT GUIDELINE>



PRECAUTIONS

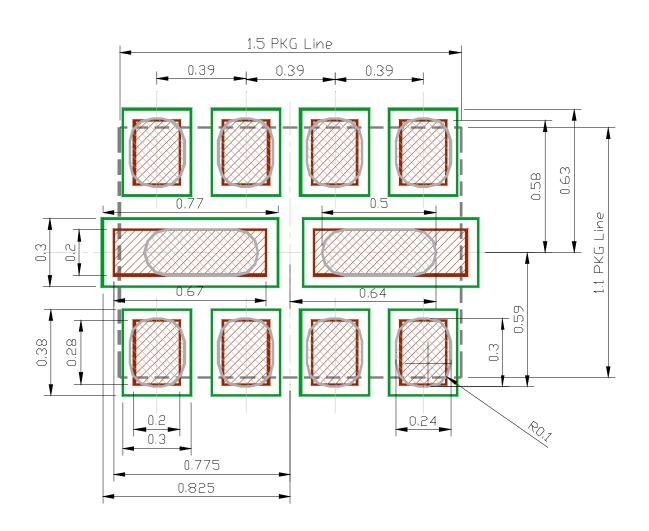
- Please layout ground pattern under this FEM in order not to couple with RFIN and RFOUT terminal.
- All external parts should be placed as close as possible to the FEM.
- For good RF performance, all GND terminals must be connected to PCB ground plane of substrate, and via-holes for GND should be placed near the FEM.

L. <u>RECOMMENDED FOOTPRINT PATTERN</u>:

PKG: 1.5 mm x 1.1 mm Pin pitch: 0.39 mm 💹 : Land

 $\ref{minipage}$: Mask (Open area) *Metal mask thickness: 100 μm

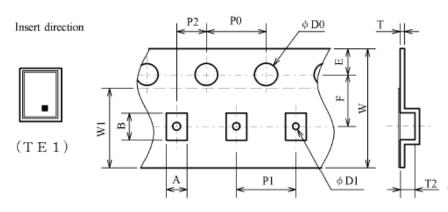
: Resist (Open area)



M. PACKING SPECIFICATION:

[TAPING DIMENSION]

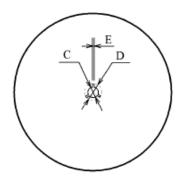
Brawing Direction

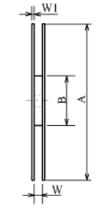


| SYMBOL | DIMENSION | REMARKS |
|--------|----------------|-------------------|
| A | 1.4±0.1 | BOTTOM DIMENSION |
| В | 1.8±0.1 | BOTTOM DIMENSION |
| D0 | 1.5 +0.1 | |
| D1 | 0.5 ± 0.05 | |
| E | 1.75±0.1 | |
| F | 3.5±0.05 | |
| P0 | 4.0±0.1 | |
| P1 | 4.0±0.1 | |
| P2 | 2.0±0.05 | |
| Т | 0.25±0.05 | |
| T2 | 0.7±0.1 | |
| W | 8.0±0.2 | |
| W1 | 5.3±0.2 | THICKNESS100µmMAX |

*Carrier tape material: PS (Anti-static) Cover tape material: PET (Anti-static)

[REEL DIMENSION]

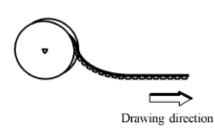


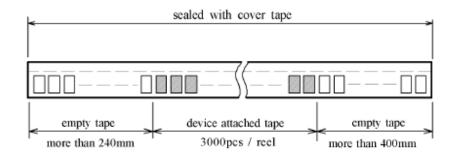


| DIMENSION |
|-----------------------------|
| φ 180 ⁺⁰ -1.5 |
| φ 66±0.5 |
| φ 13±0.2 |
| φ 21±0.8 |
| 2±0.5 |
| 9 ^{+1.0} |
| 1.2 |
| |

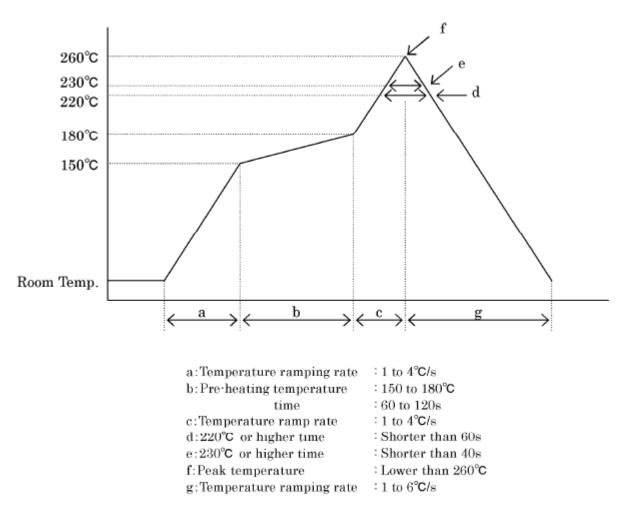
*MATERIAL : PS carbon (Anti-static)

[TAPING STATE**]**





N. <u>RECOMMENDED REFLOW PROFILE</u>:



* Recommended reflow soldering procedure

The temperature indicates at the surface of mold package.

Cautions on using this product

- This product contains Gallium-Arsenide (GaAs) which is a harmful material.
- Do NOT eat or put into mouth.
- Do NOT dispose in fire or break up this product.
- Do NOT chemically make gas or powder with this product.
- To waste this product, please obey the relating law of your country.

This product may be damaged with electric static discharge (ESD) or spike voltage. Please handle with care to avoid these damages.